

Description

The DCSM24C is a bi-directional TVS diode array, utilizing leading monolithic silicon technology to provide fast response time and low ESD clamping voltage, making this device an ideal solution for protecting sensitive semiconductor components from damage. The DCSM24C complies with the IEC 61000-4-2 (ESD) standard with $\pm 30\text{kV}$ air and $\pm 30\text{kV}$ contact discharge. It is assembled into a lead-free SOT-23 package. It is designed to protect components which are connected to data and transmission lines from voltage surges.

Features

- ◆ Protects two uni-directional lines
- ◆ Ultra low leakage: nA level
- ◆ Operating voltage: 24V
- ◆ Low clamping voltage
- ◆ Complies with following standards:
 - IEC 61000-4-2 (ESD) immunity test
 - Air discharge: $\pm 30\text{kV}$
 - Contact discharge: $\pm 30\text{kV}$
 - IEC61000-4-5 (Lighting) 6A (8/20 μs)
- ◆ RoHS Compliant

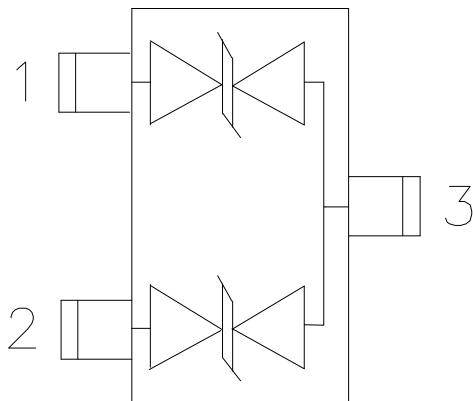
Mechanical Characteristics

- ◆ Package: SOT-23
- ◆ Lead Finish: Matte Tin
- ◆ Case Material: "Green" Molding Compound.
- ◆ Moisture Sensitivity: Level 3 per J-STD-020
- ◆ Terminal Connections: See Diagram Below
- ◆ Marking Information: See Below

Applications

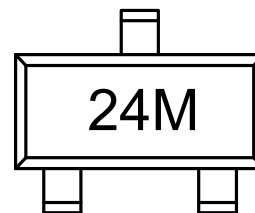
- ◆ Cellular Handsets and Accessories
- ◆ Notebook and Handhelds
- ◆ Portable Instrumentation
- ◆ Set Top Box
- ◆ Industrial Controls
- ◆ Server and Desktop PC

Dimensions and Pin Configuration



Circuit and Pin Schematic

Marking Information



24M = Device Marking Code

Ordering Information

Part Number	Marking	Packaging	Reel Size
DCSM24C	24M	3000/Tape & Reel	7 inch

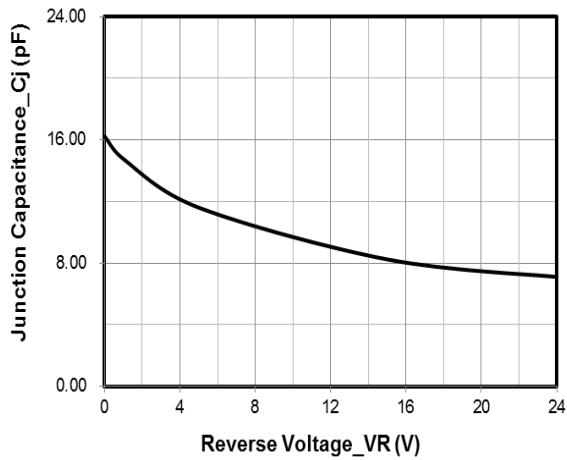
Absolute Maximum Ratings ($T_A=25^{\circ}\text{C}$ unless otherwise specified)

Parameter	Symbol	Value	Unit
ESD per IEC 61000-4-2 (Air)	V_{ESD}	± 30	kV
ESD per IEC 61000-4-2 (Contact)		± 30	
Operating Temperature Range	T_J	-55 to +125	$^{\circ}\text{C}$
Storage Temperature Range	T_{stg}	-55 to +150	$^{\circ}\text{C}$

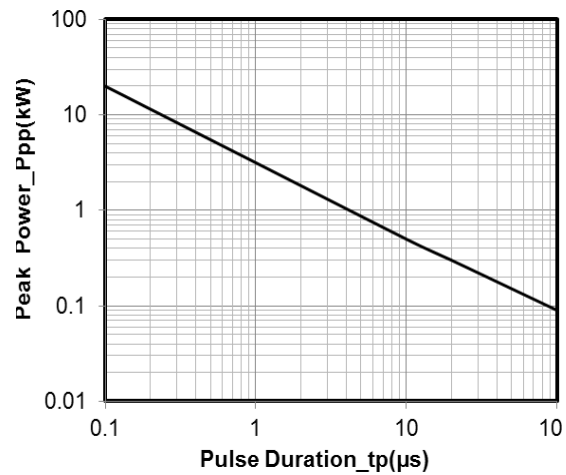
Electrical Characteristics ($T_A=25^{\circ}\text{C}$ unless otherwise specified)

Parameter	Symbol	Min	Typ	Max	Unit	Test Condition
Reverse Working Voltage	V_{RWM}			24	V	
Breakdown Voltage	V_{BR}	26.7		32	V	$I_T = 1\text{mA}$
Reverse Leakage Current	I_{R}			500	nA	$V_{\text{RWM}} = 24\text{V}$
Clamping Voltage	V_{C}		30	36	V	$I_{\text{PP}} = 1\text{A}$ (8 x 20 μs pulse)
Clamping Voltage	V_{C}		43	50	V	$I_{\text{PP}} = 6\text{A}$ (8 x 20 μs pulse)
Junction Capacitance	C_J			20	pF	$V_{\text{R}} = 0\text{V}$, $f = 1\text{MHz}$, Pin 1 to Pin 3 or Pin 2 to Pin 3

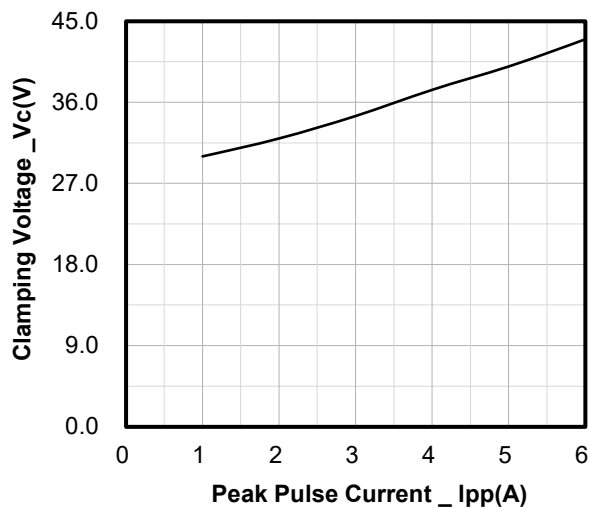
Typical Performance Characteristics (TA=25°C unless otherwise Specified)



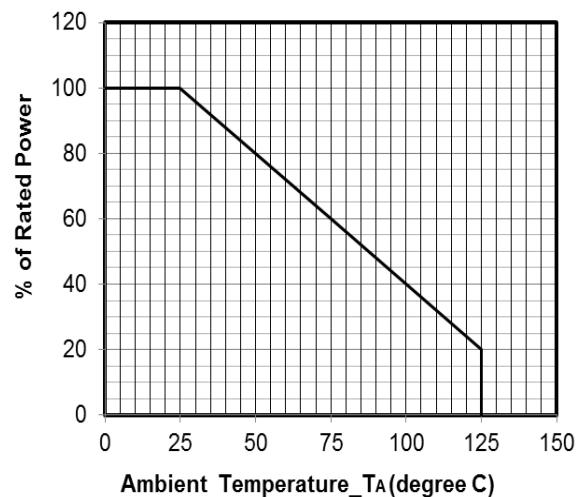
Junction Capacitance vs. Reverse Voltage



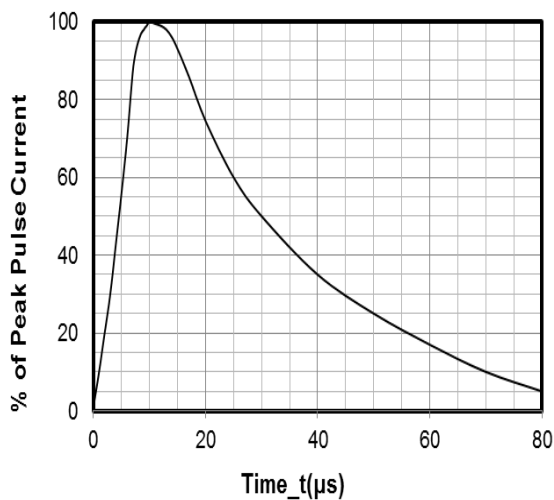
Peak Pulse Power vs. Pulse Time



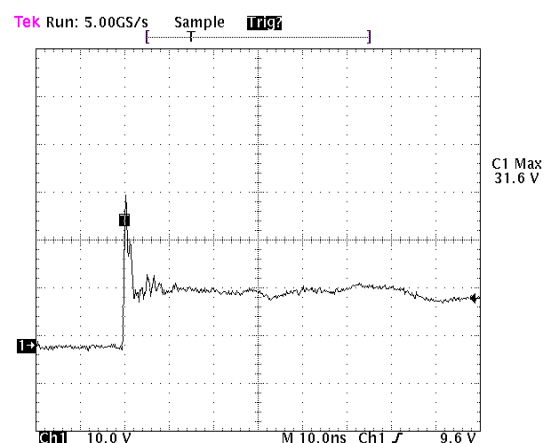
Clamping Voltage vs. Peak Pulse Current



Power Derating Curve



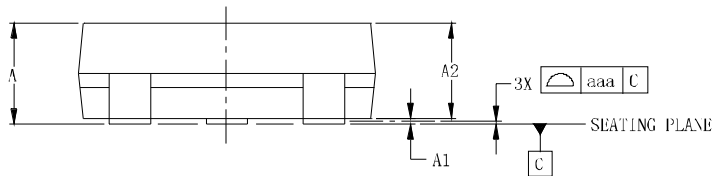
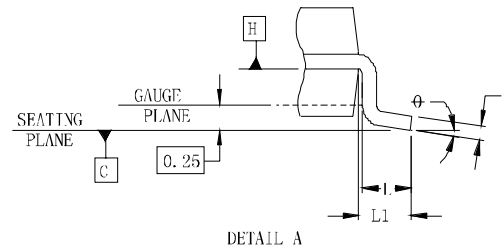
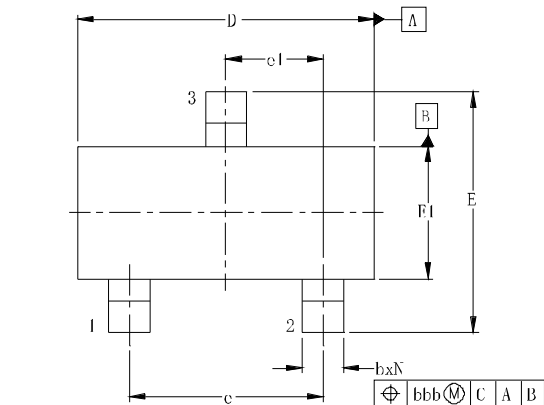
8 X 20 μ s Pulse Waveform



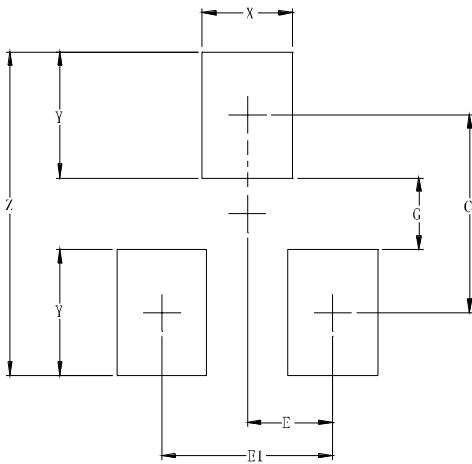
Note: Data is taken with a 10x attenuator

ESD Clamping Voltage
8 kV Contact per IEC61000-4-2

SOT-23 Package Outline Drawing



Suggested Land Pattern



Contact Information

Changzhou D-first Electronics Co.,Ltd.

www.first-electronic.com

Email: xinghongfei@first-electronic.com

Phone: +86 (0519) 8817 1671

DIMENSIONS

SYM	INCHES			MILLIMETERS		
	MIN	NOM	MAX	MIN	NOM	MAX
A	0.035	-	0.044	0.89	-	1.12
A1	0.000	-	0.004	0.01	-	0.10
A2	0.035	0.037	0.040	0.88	0.95	1.02
b	0.012	-	0.020	0.30	-	0.51
c	0.003	-	0.007	0.08	-	0.18
D	0.110	0.114	0.120	2.80	2.90	3.04
E	0.082	0.093	0.104	2.10	2.37	2.64
E1	0.047	0.051	0.055	1.20	1.30	1.40
e	0.075			1.90BSC		
e1	0.037			0.95BSC		
L	0.015	0.020	0.024	0.40	0.50	0.60
L1	0.022			0.55		
N	3			3		
θ	0°	-	8°	0°	-	8°
aaa	0.004			0.10		
bbb	0.008			0.20		

DIMENSIONS

SYM	INCHES	MILLIMETERS
C	0.087	2.20
E	0.037	0.95
E1	0.075	1.90
G	0.031	0.80
X	0.039	1.00
Y	0.055	1.40
Z	0.141	3.60